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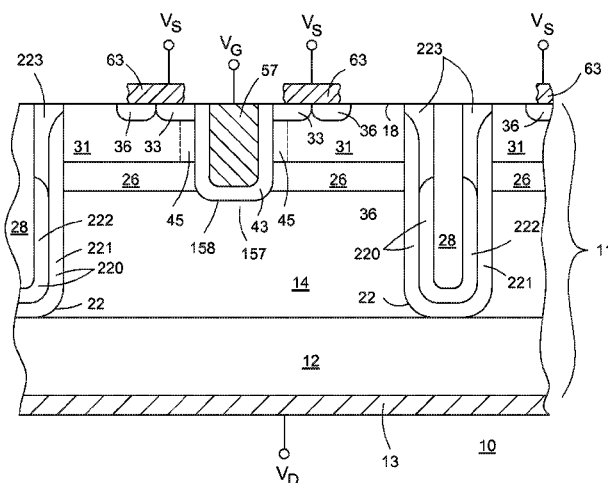
(57) **ABSTRACT**

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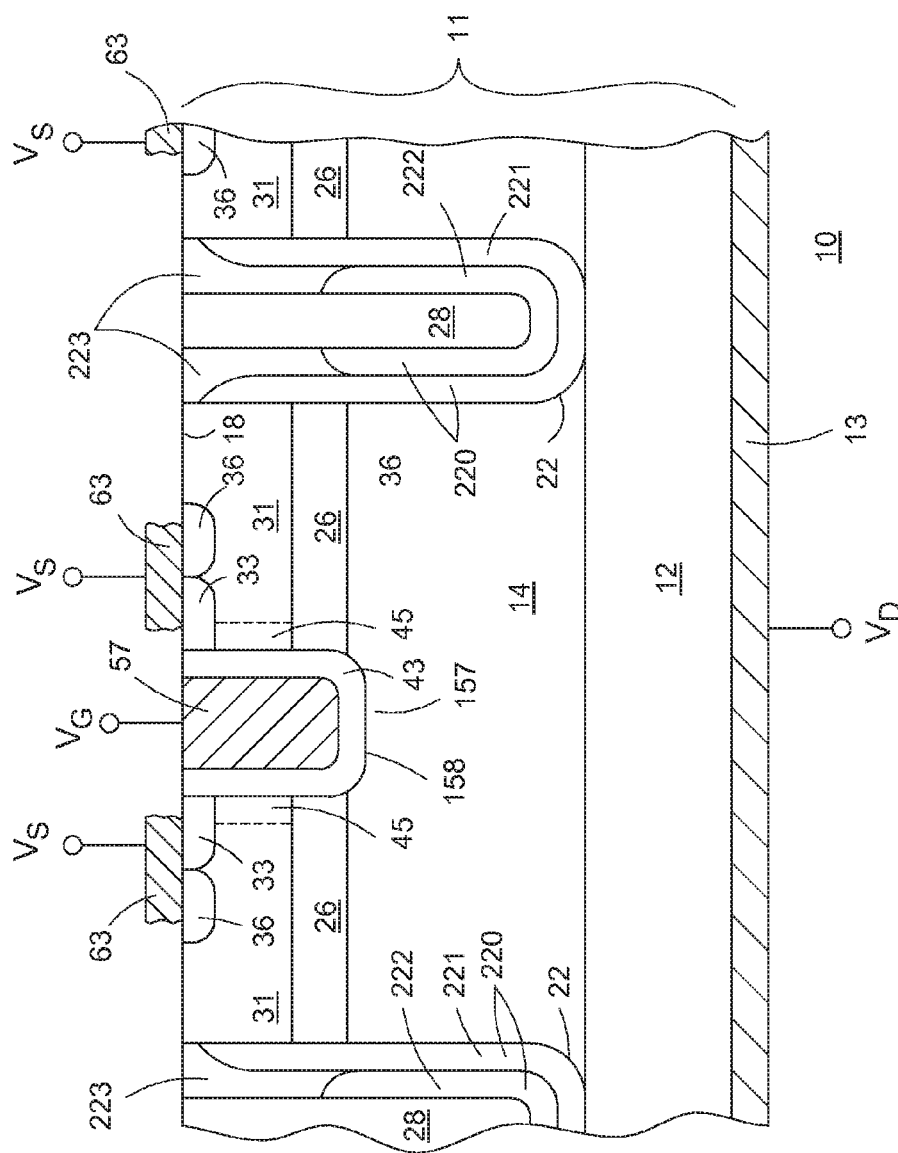


FIG. 1

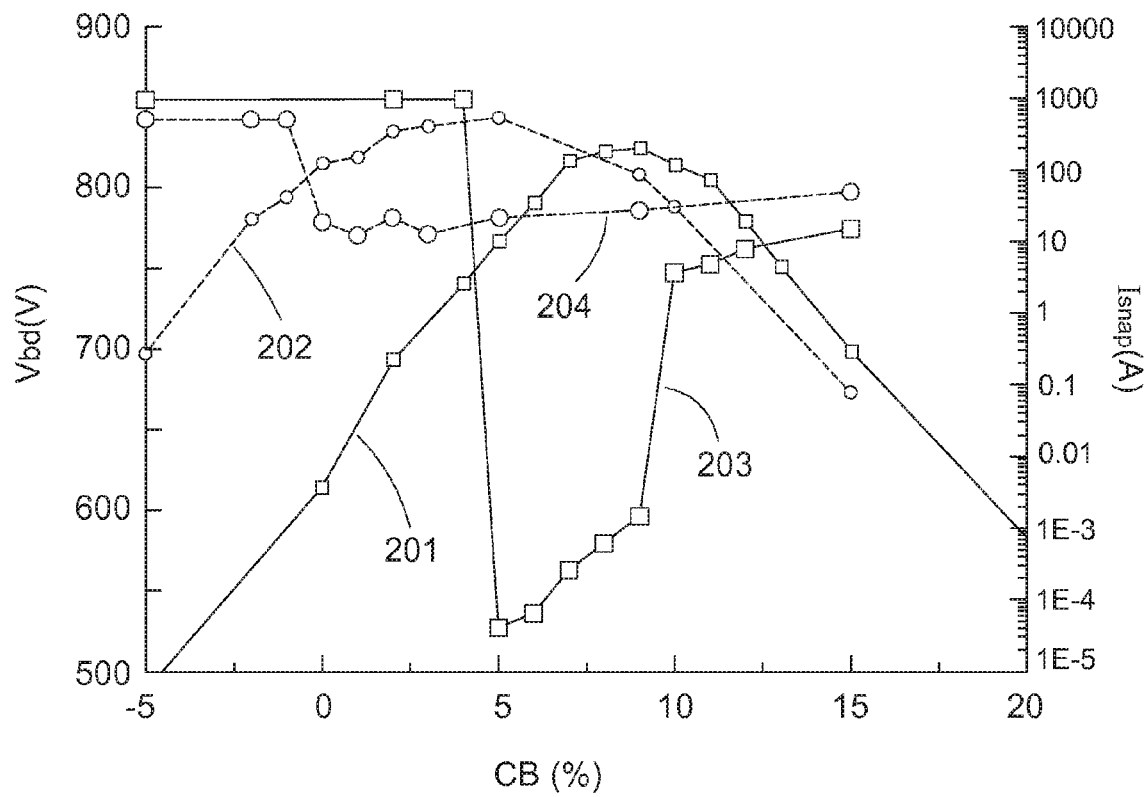
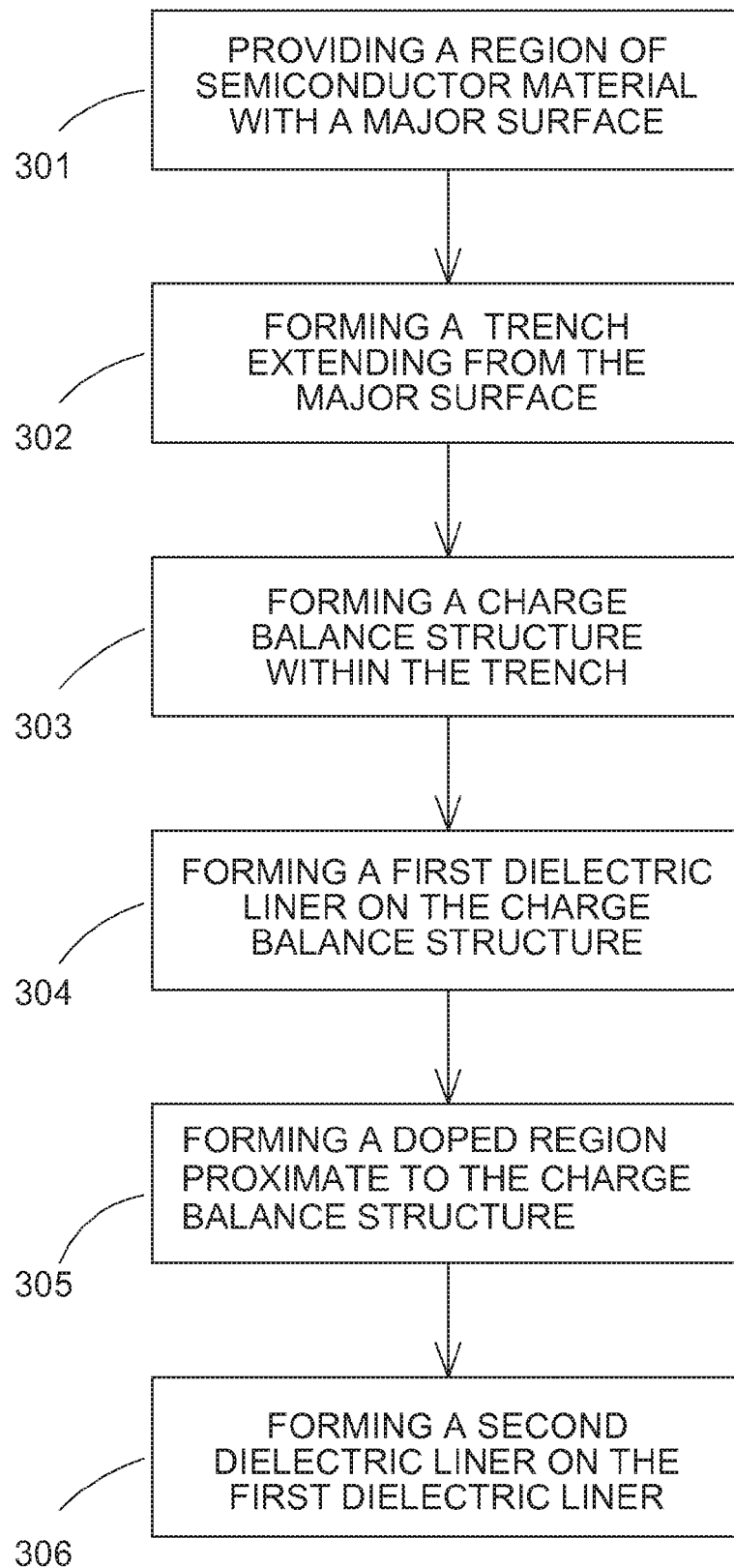


FIG. 2

*FIG. 3*

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SEMICONDUCTOR DEVICE HAVING LOCALIZED CHARGE BALANCE STRUCTURE AND METHOD

CROSS REFERENCE TO RELATED APPLICATION

This application claims the benefit of priority from U.S. Provisional Application No. 61/710,526, which was filed on Oct. 5, 2012, and fully incorporated herein.

BACKGROUND

The present invention relates, in general, to electronics and, more particularly, to methods of forming semiconductors and structures therefore.

Metal-oxide semiconductor field effect transistors (MOSFETs) are a common type of power switching device. A MOSFET device includes a source region, a drain region, a channel region extending between the source and drain regions, and a gate structure provided adjacent to the channel region. The gate structure includes a conductive gate electrode layer disposed adjacent to and separated from the channel region by a thin dielectric layer.

When a MOSFET device is in the on state, a voltage is applied to the gate structure to form a conduction channel region between the source and drain regions, which allows current to flow through the device. In the off state, any voltage applied to the gate structure is sufficiently low so that a conduction channel does not form, and thus current flow does not occur. During the off state, the device must support a high voltage between the source region and the drain region.

Today's higher voltage power switch market is driven by at least two major parameters, which include breakdown voltage (BV_{dss}) and on-state resistance (R_{dson}). For a specific application, a minimum breakdown voltage is required, and in practice, designers typically can meet a BV_{dss} specification. However, this is often at the expense of R_{dson}. This trade-off in performance is a major design challenge for manufacturers and users of high voltage power switching devices.

Recently, superjunction devices have gained in popularity to improve the trade-off between R_{dson} and BV_{dss}. In previous n-channel superjunction devices, multiple heavily-doped diffused n-type and p-type regions replace one lightly doped n-type epitaxial region. In the on state, current flows through the heavily doped n-type regions, which lowers R_{dson}. In the off or blocking state, the heavily doped n-type and p-type regions deplete into or compensate each other to provide a high BV_{dss}. More recently, price points for superjunction devices have become more attractive and market trends are driving demand for lower conduction and switching losses. Additional factors driving demands for superjunction devices include increased power conversion efficiency, increased power density requirements, smaller package requirements with demand for better performance, adoption of surface mount packages, and reductions in heat sinking requirements.

Although superjunction devices look promising, significant challenges still exist in manufacturing them. Another problem with previous superjunction devices is that the energy capability (E_{as}) under unclamped inductive switching (UIS) testing is often too low under optimum charge balance (for example, charge balance (CB) approaching 0%) or within a desired charge balance window. Such inadequate E_{as} capability is believed to be from low snapback current (I_{snappback}) in the reverse blocking IdVd curve. A low I_{snappback}

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can produce a pure electrical failure observed at few nano-seconds after switching-off the device in the typical UIS test. The electrical failure can occur when a negative differential resistance is reached at a certain region of the active area, thus producing a non-uniform current distribution and, eventually, a current focalization or a "hot spot". Additionally, a low I_{snappback} can limit the energy capability under other tests, such as reverse recovery tests.

Accordingly, it is desirable to have a structure for and method of making a superjunction semiconductor device that improves UIS performance. It would be beneficial if the structure and method maintained the design trade-offs between UIS, R_{dson}, and BV_{dss}. Additionally, it would be beneficial if the structure and method did not add significant process complexity or excessive costs.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 illustrates a partial cross-sectional view of a semiconductor device in accordance with an embodiment of the present invention;

FIG. 2 illustrates graphical information of reverse current-voltage (I-V or IV) characteristics comparing a semiconductor device in accordance with the present invention with a prior structure; and

FIG. 3 illustrates an embodiment of a process flow for manufacturing a semiconductor device in accordance with the present invention.

For simplicity and clarity of the illustration, elements in the figures are not necessarily drawn to scale, and the same reference numbers in different figures denote the same elements. Additionally, descriptions and details of well-known steps and elements are omitted for simplicity of the description. For clarity of the drawings, certain regions of device structures, such as doped regions or dielectric regions, may be illustrated as having generally straight line edges and precise angular corners. However, those skilled in the art understand that, due to the diffusion and activation of dopants or formation of layers, the edges of such regions generally may not be straight lines and that the corners may not be precise angles.

Furthermore, the term "major surface" when used in conjunction with a semiconductor region, wafer, or substrate means the surface of the semiconductor region, wafer, or substrate that forms an interface with another material, such as a dielectric, an insulator, a conductor, or a polycrystalline semiconductor. The major surface can have a topography that changes in the x, y and z directions.

DETAILED DESCRIPTION OF THE DRAWINGS

Certain previous superjunction technologies are based on a local charge balanced (LCB) concept. By way of example, in LCB devices superjunction trenches can be formed by reactive ion etching in the active area of a semiconductor substrate and then lined with as-formed heavily-doped n-type and p-type layers. In one embodiment, an n-type layer is formed first, and then a p-type layer is formed thereafter. Typically, both the n-type and p-type doping is uniform along the entire superjunction trench depth. Thus, because there is no imbalance along the superjunction trench depth the electric field is therefore uniform for optimum charge balance and highest breakdown voltage. However, this configuration has been found to be underperforming for UIS conditions (where high avalanche current densities can occur) because of what is termed the Egawa effect. UIS performance data for previous 650 volt LCB devices has shown that for a charge balance (CB) of 0%, breakdown voltage (BV_{dss}) ranges from about

650 volts (V) to about 750V, but UIS ranges from close to zero (0) milli-Joules/cm² (mJ/cm²) to just above 650 mJ/cm², which is below desired target specifications. This data illustrates that an undesirable UIS performance can occur around an optimum charge balance condition where maximum breakdown can occur. Specifically, for an optimum charge balance and maximum breakdown voltage, the UIS robustness is near zero. This illustrates the problem to be addressed by the present embodiments that utilize a sufficiently tailored charge balanced structure in order to enhance UIS performance to be more acceptable.

The present description discloses a configuration that improves UIS performance, for example, in LCB superjunction structures. In the present description, the configuration is described in two representative embodiments both configured to create an imbalanced superjunction structure across a selected CB window. Stated another way, the present embodiments are configured to unbalance the dopant profiles in a selected location(s) in or proximate to the superjunction structure or column(s) so as to modify the electric field distribution along the superjunction column. The modified electric field has a less than flat profile or has a less than uniform profile along the superjunction column over the selected CB window. The present embodiments are configured to address the UIS robustness issues observed in previous superjunction embodiments.

The two example embodiments include electric field tailoring using ion implantation or a connection implant into upper portions of the superjunction structures, and electric field tailoring by using intrinsic-epitaxial (i-epi) dopant profile tailoring adjacent to the superjunction structures. Both embodiments are based, at least in part, on electric field (E-field) engineering such that the resultant E-field along the superjunction trench is purposely imbalanced. As a result, when minority and majority carriers are flowing in the device under avalanche conditions, minority and majority carriers do not significantly alter the E-field in such a way that the E-field becomes completely flat (as in an optimum charge balanced condition in previous devices). A flat E-field is believed to lead to the Egawa effect (also termed "E-field quenching"), which can lead to early destruction of the device due to current crowding effects.

In accordance with the present embodiments, the induced non-uniform electric field can allow the voltage (that is, the area under the electric field distribution) to increase when the drift region is flooded with excess majority and minority carriers under avalanche conditions (for example, during a UIS test). Hence, the I-V characteristics of the present embodiments exhibit positive differential resistance (PDR), balancing the current—in contrast to negative differential resistance (NDR) found in previous devices, which can cause filamentation and destruction. The current level at which the NDR sets in is called the snapback current (Isnapback). The present embodiments as described subsequently are configured to increase the snapback current by, for example, delaying the NDR in the reverse I-V characteristic. Although the following embodiments are described as an n-channel device, those skilled in the art will appreciate that the present embodiments are suitable for p-channel devices by reversing the described conductivity types or for complementary configurations.

FIG. 1 shows a partial cross-sectional view of an insulated gate field effect transistor (IGFET), MOSFET, LCB superjunction device, superjunction structure, charged-compensated, LCB structure, or switching device or cell 10 in accordance with a first embodiment that is configured to address the issues with prior devices described previously as well as

others. By way of example, device 10 is among many such devices integrated with logic and/or other components into a semiconductor chip as part of a power integrated circuit. Alternatively, device 10 is among many such devices integrated together to form a discrete transistor device.

Device 10 includes a region of semiconductor material 11, which comprises for example, an n-type silicon substrate 12 having a resistivity in a range of approximately 0.001 to about 0.01 ohm-cm, and may be doped with arsenic or phosphorous. In the embodiment shown, substrate 12 provides a drain region for device 10, which is adjacent to a conductive layer 13. A semiconductor layer 14 is formed in, on, or overlying substrate 12 and can be n-type and doped light enough in one embodiment so as to not impact charge balance in the trench compensation regions described below. In one embodiment, layer 14 is formed using epitaxial growth techniques. In an embodiment suitable for a 650 volt device, layer 14 is doped n-type with a dopant concentration of about 1.0×10^{13} atoms/cm³ to about 5.0×10^{14} atoms/cm³, and has a thickness on the order of about 40 microns to about 70 microns. Note that, although semiconductor layer 14 is shown as thicker than substrate 12 in the drawings, substrate 12 can be thicker. It is shown this way for ease of understanding in the drawings. The thickness of layer 14 is increased or decreased depending on the desired BV_{dss} rating of device 10. Additionally, those skilled in the art will understand that an insulated gate bipolar transistor (IGBT) device is achieved with the present structure by, for example, changing the conductivity type of substrate 12 to p-type (i.e., opposite to semiconductor layer 14). In an optional embodiment, substrate 12 may further include an n+ type buffer layer that is formed prior to semiconductor layer 14.

Device 10 further includes spaced apart filled trenches, compensating trenches, semiconductor material filled trenches, charge-compensated trench regions, LCB regions, LCB structures, charge-compensated filled trenches, compensation trenches, localized vertical charge compensation structures, or LCB regions or pillars 22. As used herein, charge compensation generally means that the total charge of the opposite conductivity type layers is substantially or generally balanced or equal. Charge-compensated filled trenches 22 include a plurality of layers or multiple pillars of material, conductive material or semiconductor material 220, including at least two layers, structures, or pillars of opposite conductivity type (i.e., at least one each of n-type and p-type), which may be separated by an intrinsic, buffer, or lightly doped semiconductor layer or layers. As shown in FIG. 1, material 220 includes a pillar or layer 221 of n-type semiconductor material adjoining semiconductor layer 14 along sidewall surfaces of the trenches.

In accordance with a one embodiment, layers 221 are of the same conductivity type as source regions 33, and form a primary vertical low resistance current path from the channel to the drain when device 10 is in the on-state. A layer 222 of compensating p-type semiconductor material is formed overlying layer 221. By way of example, n-type layers 221 and p-type layers 222 can have a dopant concentration on the order of about 1.0×10^{15} atoms/cm³ to about 1.0×10^{17} atoms/cm³, and each can have a thickness of about 0.1 microns to about 0.4 microns. Depending on the desired charge balance, the foregoing dopant concentrations are increased or decreased accordingly. When device 10 is in an off state, p-type layers 222 and n-type layers 221 compensate each other to provide an increased BV_{dss} characteristic. Although no intrinsic or buffer layers are shown in the device of FIG. 1, it is understood that they may be present in earlier steps in fabrication and may not be as evident because dopant can

diffuse into such layers during subsequent high temperature processing. In one embodiment, layers of semiconductor material **220** comprise a single crystalline semiconductor material and have as-formed dopant profiles.

In one embodiment, device **10** also includes one or more dielectric layers or a dielectric plug, or dielectric liner **28** formed overlying pillars **220** within trenches **22**. In one embodiment, dielectric layer **28** is a deposited silicon oxide layer. In one embodiment, dielectric layer **28** can be multiple dielectric layers deposited or formed at different steps and can be different materials. Although not shown, it is understood that during the formation of device **10**, n-type dopant from highly doped substrate **12** can diffuse into the lower portions of LCB trenches **22** so that those portions of trenches **22** within substrate **12** become more heavily doped n-type. When the optional n+ type buffer layer is used in conjunction with substrate **12**, trenches **22** preferably extend into the n+ type buffer layer.

In accordance with the present embodiment, device **10** further includes imbalanced regions, doped regions, p-connection regions, top p-connection regions, or implanted regions **223** formed proximate to, at or along upper portions of trenches **22**. Doped regions **223** are configured to make the top or upper portions of trenches **22** higher doped and in the case of the present embodiment, more p-dopant rich or p-rich. In one embodiment, a p-type (or n-type when device **10** is configured as a p-channel device) connection ion implant using a predetermined implant angle(s) to implant dopant into the superjunction trench area can be used to form doped regions **223** to create a charge imbalance in LCB trenches **22**. In one embodiment, about the upper 5 to 15 microns of the device can be made more p-rich in the superjunction trench area. In one embodiment, about the upper 10 microns of the device can be made more p-rich. In the present embodiment, an ion implant dose in a range from about 2.0×10^{12} atoms/cm² to about 5.0×10^{13} atoms/cm² can be used. In accordance with a first embodiment, an angled top boron implant can be performed into a charge balanced structure. The implant is such that part of the charge balanced structure is deliberately made more p-rich compared to previous structures to intentionally create a charge imbalance.

Additionally, it was observed that the charge imbalance along the superjunction column can be adjusted using different implant angles to form doped regions **223**. For example, in one embodiment using a 200 KeV, 6.0×10^{12} atoms/cm² dose and a 5 degree implant angle, the top 10 microns of the superjunction column are approximately 25% p-rich. As a result, the electric field remains less than flat (optimum) over a 25% charge imbalance window. In an alternative embodiment, the implant step can be done in multiple twist angles. In one embodiment, the implant step can be done with either two twist angles or four twist angles with a tilt angle of a few degrees.

Device **10** also includes a well, base, body or doped regions **31** formed in semiconductor layer **14** between and in proximity to, adjacent to, or adjoining LCB trenches **22**. Body regions **31** can extend from major surface **18** of semiconductor material **11**. In one embodiment, body regions **31** comprise p-type conductivity, and have a dopant concentration suitable for forming an inversion layer that operates as conduction channels **45** of device **10**. Body regions **31** extend from major surface **18** to a depth of about 1.0 to about 5.0 microns. Those skilled in the art will appreciate that body regions **31** can comprise a plurality of individually diffused regions, or comprise a connected, single or commonly diffused region of selected shape, or can comprise combinations thereof.

N-type source regions **33** are formed within, above, or in body regions **31** and extend from major surface **18** to a depth of about 0.2 microns to about 0.5 microns. In one embodiment, portions of major surface **18** extend down and then outward from the edges of source regions **33** so that contact is made to horizontal and vertical surfaces of source regions **33** by source contact layer **63**. One or more p-type body contact regions **36** are formed in at least a portion of each body region **31**. Body contact regions **36** are configured to provide a lower contact resistance to body region **31**, and to lower the sheet resistance of body regions **31** under source regions **33**, which suppresses parasitic bipolar effects.

Device **10** further includes a trench gate or control structure **157** adjoining body regions **31** and source regions **33**. Control structure **157** is laterally spaced apart from adjacent charge-compensated trench **22**. That is, control structure **157** does not overlie charge-compensated trench **22**. Trench gate structure **157** includes a gate trench **158** and a gate dielectric layer **43** formed overlying surfaces of gate trench **158**. In one embodiment, gate dielectric layer **43** comprises a silicon oxide, and has a thickness of about 0.05 microns to about 0.1 microns. In another embodiment, gate dielectric layer **43** has a thickness at the lower surfaces of gate trench **158** that is greater or thicker than the thickness of gate dielectric layer **43** along the sidewalls of gate trench **158**. In alternative embodiments, gate dielectric layer **43** comprises silicon nitride, tantalum pentoxide, titanium dioxide, barium strontium titanate, or combinations thereof including combinations with silicon oxide, or the like.

Trench gate structure **157** further includes a conductive gate region **57** formed within control or gate trench **158** and overlies gate dielectric layer **43**. In one embodiment, a source region **33** is interposed between a conductive gate region **57** and a charge compensation trench **22**. Conductive gate region **57** comprises, for example, n-type polysilicon. Although conductive gate region **57** is shown as substantially co-planar with major surface **18**, conductive gate region **57** may extend higher or above major surface **18** or may be recessed below major surface **18**. Trench gate structure **157** is configured to control the formation of channels **45** and the conduction of current in device **10**.

To facilitate a sub-surface current path, device **10** can further include n-type link, n-type doped layers or sub-surface doped layers **26**. Specifically, doped layers **26** are configured to provide a sub-surface conduction path (i.e., horizontally-oriented conduction or current path) between the drain ends of channels **45** and n-type layers **221**, which are the primary conduction layers or vertical conduction or current paths in LCB trenches **22**. That is, in device **10** current flows vertically through channels **45**, then horizontally through doped layers **26**, and then vertically through layers **221**. Doped layers **26** are configured so that current flow is isolated from major surface **18** by body regions **31** and body contact regions **36**, which are opposite conductivity types (p-type) from doped layers **26** (n-type).

Source contact layer **63** is formed overlying major surface **18** and makes contact to both source regions **33** and body contact regions **36**. Although shown as a partial layer, it is understood that source contact layer **63** can overlie major surface **18** and is isolated from gate electrode **57** by an inter-layer dielectric structure (not shown). In one embodiment, source contact layer **63** comprises a titanium/titanium nitride barrier layer and an aluminum silicon alloy formed overlying the barrier layer, or other materials known to those of skill in the art. Drain contact layer **13** is formed overlying an opposing surface of semiconductor material **11**, and comprises, for

example, a solderable metal structure such as titanium-nickel-silver, chrome-nickel-gold, or the like.

The operation of device 10 proceeds as follows. Assume that source terminal 63 is operating at a potential V_S of zero volts, conductive gate regions 157 receive a control voltage $V_G=5.0$ volts, which is greater than the conduction threshold of device 10, and drain terminal 13 operates at drain potential $V_D=5.0$ volts. The values of V_G and V_S cause body region 31 to invert adjacent conductive gate regions 157 to form vertical channels 45, which electrically connect source regions 33 to doped regions 26. A device current I_d flows from drain terminal 13 and is routed through n-type pillars 221, doped layer 26, channels 45, source regions 33, to source terminal 63. Hence, current I_d flows vertically through n-type pillars 221 to produce a low on-resistance, and horizontally through n-type links 26 keeping the current path isolated from major surface 18. In one embodiment, $I_d=1.0$ amperes. To switch device 10 to the off state, a control voltage V_G of less than the conduction threshold of the device is applied to conductive gate regions 157 (e.g., $V_G<5.0$ volts). This removes channels 45 and I_d no longer flows through device 10. In the off state, n-type pillars 221 and p-type pillars 222 compensate each other as the depletion region from the primary blocking junction spreads, which enhances BV_{dss} .

FIG. 2 illustrates graphical information including breakdown voltage and snapback current as a function of charge balance comparing device 10 of the present embodiment to a previous device. Curve 201 is breakdown voltage for a prior device that does not have doped regions 223, curve 202 is breakdown voltage for device 10 with doped regions 223, curve 203 is snapback current for a prior device that does not have doped regions 223, and curve 204 is snapback current for device 10 with doped regions 223. In comparing curves 203 and 204 in FIG. 2, it is illustrated that doped regions 223 provide a charge imbalance that results in a reduction of NDR in the I-V characteristic, leading to higher snapback currents (lack of U-shape in $I_{snapback}$ curve 204 compared to curve 203) hence better UIS capability. In one embodiment, the snapback current (onset of NDR) improves by over 5 decades compared to previous devices.

In other embodiments, it was observed that a 3 degree implant angle (using, for example, an ion implant dose of 6.0×10^{12} atoms/cm² at 200 KeV) made approximately the top 20 microns of the superjunction column approximately 14% p-rich, a 7 degree implant angle made approximately the top 7 microns of the superjunction column approximately 33% p-rich, a 10 degree implant angle made approximately the top 5 microns of the superjunction column approximately 50% p-rich, and a 20 degree implant angle made approximately the top 3 microns of the superjunction column approximately 150% p-rich.

Additionally, UIS studies of device 10 showed that device 10 having doped regions 223 improved UIS robustness (for example, greater than 600 milli Joules (mJ)) compared to prior devices that do not have doped regions 223 (for example, approaching 0 mJ). Further, it was observed that the breakdown voltage distribution of device 10 has a more narrow distribution compared to previous devices that do not include doped regions 223, which is believed to be due to the purposely induced field imbalance in accordance with the present embodiment.

FIG. 3 illustrates a process sequence to form doped regions 223 in a connection implant in accordance with an embodiment of the present invention. In a first step 301, region of semiconductor material 11 is provided with a hard mask formed on major surface 18. By way of example, the hard mask can be oxide-nitride-oxide configuration. Openings are

then formed in the hard mask layer to expose portions of major surface 18 where trenches 22 will be formed.

In step 302, a trench etch is used to form trenches 22 extending from major surface 18 of region of semiconductor material 11. In one embodiment, Deep Reactive Ion Etching (DRIE) etching with a fluorine or chlorine based chemistry can be used to form trenches 22. Several techniques are available for DRIE etching trenches 22 including cryogenic, high-density plasma, or Bosch DRIE processing. In step 303, a superjunction structure, such as LCB structure 220, can then be formed within trenches 22. In one embodiment, an intrinsic epi—n-type epi—intrinsic epi—p-type epi—intrinsic epi pillar structure can be formed. In one embodiment, the superjunction structure is formed to be charge balanced. In step 304, a first dielectric liner can then be formed over the charge balanced structure. In one embodiment, an oxide can be used. In step 305, a connection implant or p-type implant can be made into the superjunction structure to form doped region 223 to connect body region 31 to the p-type pillar 222 and to create the charge imbalance of the present embodiment at a selected implant angle or angles as described previously. In step 306, a second dielectric liner can then be formed over the first dielectric liner to form dielectric structure 28.

In another embodiment, charge imbalancing of the superjunction column 222 can also be achieved by tailoring the doping profile of semiconductor layer 14 adjoining the superjunction trench 22, which can be intrinsic epi or i-epi. In accordance with the second embodiment, semiconductor layer 14 is provided with a non-uniform dopant profile. In one embodiment, semiconductor layer 14 is provided with a substantially linear graded dopant profile. In one embodiment, semiconductor layer 14 has a dopant concentration of about 8.0×10^{13} atoms/cm³ proximate to doped layers 26 of device 10, and then linearly increased over the thickness of semiconductor layer 14 towards substrate 12 to approximately 2.0×10^{13} atoms/cm³. This linear profile was observed to result in a linear variation of the CB across the superjunction column in trench 22 (for example, CB can vary over 40% across the SJ column). The resulting I-V characteristics of this embodiment showed no NDR up to very high current levels (for example, greater than 50 amps). In accordance with the present embodiment, the configuration showed that a linearly graded n-epi provides a positive differential resistance across a selected charge balance window, which improves UIS performance compared to prior superjunction devices. In a further embodiment, both doped regions 223 and the non-uniform dopant profile with semiconductor layer 14 can be used.

In view of all of the above, it is evident that a novel method and structure are disclosed. Included, among other features, is intentionally creating a charge imbalance in a LCB superjunction structure. In one embodiment, a doped region such as a p-type region is formed near an upper portion of the superjunction structure. In another embodiment, the semiconductor region adjacent to the superjunction structures has a non-uniform dopant profile with a lower dopant concentration near the upper surface of the superjunction structure and then increasing towards a lower portion of the superjunction structure. The resulting charge imbalance from the structure induces a non-uniform electric field and can allow the voltage (that is, the area under the electric field distribution) to increase when the drift region is flooded with excess majority and minority carriers under avalanche conditions (for example, during a UIS test) to improve performance. Hence, the I-V characteristic of the present embodiments exhibit positive differential resistance (PDR), balancing the current—in contrast to NDR found in previous devices, which can cause filamentation and destruction.

While the subject matter of the invention is described with specific preferred embodiments and example embodiments, the foregoing drawings and descriptions thereof depict only typical embodiments of the subject matter, and are not therefore to be considered limiting of its scope. It is evident that many alternatives and variations will be apparent to those skilled in the art. For example, described dopant conductivity types can be reversed.

As the claims hereinafter reflect, inventive aspects may lie in less than all features of a single foregoing disclosed embodiment. Thus, the hereinafter expressed claims are hereby expressly incorporated into this Detailed Description of the Drawings, with each claim standing on its own as a separate embodiment of the invention. Furthermore, while some embodiments described herein include some but not other features included in other embodiments, combinations of features of different embodiments are meant to be within the scope of the invention and meant to form different embodiments as would be understood by those skilled in the art.

We claim:

1. A semiconductor device structure comprising:

a substrate;

a first semiconductor layer overlying the substrate and having a major surface spaced apart from the substrate;

a localized superjunction structure within a portion of the first semiconductor layer and extending from the major surface into at least the first semiconductor layer, wherein the localized superjunction structure comprises:

a trench extending from the major surface into at least the first semiconductor layer, wherein the trench has a sidewall surface,

a second semiconductor layer of a first conductivity type overlying the sidewall surface of the trench, having a generally vertical orientation and adjoining the first semiconductor layer, and

a third semiconductor layer of a second conductivity type disposed within the trench, wherein the third semiconductor layer is disposed adjacent to the second semiconductor layer;

a control electrode adjacent the major surface and spaced apart from the localized superjunction structure;

a body region adjacent the major surface, the body region being laterally interposed between the control electrode and the localized superjunction structure, wherein the localized superjunction structure adjoins a vertically oriented side surface of the body region and the first semiconductor layer adjoins a bottom surface of the body region, and wherein the body region extends downward from the major surface to a first depth; and

a first doped region of the second conductivity type disposed extending from the major surface to a top surface of the third semiconductor layer, wherein the first doped region has a higher dopant concentration than the third semiconductor layer and is configured to provide a charge imbalance within the localized superjunction structure, and wherein:

a first portion of the first doped region overlaps a top portion of the second semiconductor layer to laterally connect the body region to the third semiconductor layer, the first portion of the first doped region abutting the vertically oriented side surface of the body region,

the first doped region extends vertically downward from the major surface to a second depth greater than the first depth, and

the top portion of the second semiconductor layer separates a second portion of the first doped region from at least a portion of the vertically oriented side surface of the body region, the second portion of the first doped region being different from the first portion of the first doped region.

2. The semiconductor device structure of claim 1, further comprising:

a dielectric structure disposed within the trench and disposed adjacent the third semiconductor layer, wherein the dielectric structure comprises a first dielectric liner and a second dielectric liner overlying the first dielectric liner.

3. The semiconductor device structure of claim 2, wherein the second depth is between 5 microns and 15 microns.

4. The semiconductor device structure of claim 1, wherein the higher dopant concentration of the first doped region provides the charge imbalance between 5% and 10%.

5. The semiconductor device structure of claim 1, wherein: the substrate comprises the first conductivity type; and the body region comprises the second conductivity type.

6. The semiconductor device structure of claim 1, wherein the charge imbalance within the localized superjunction structure is greater than or equal to approximately fourteen percent.

7. A semiconductor device structure comprising:

a region of semiconductor material having a major surface; a trench extending from the major surface into the region of semiconductor material, wherein the trench has a sidewall surface;

a first semiconductor layer of a first conductivity type overlying the sidewall surface of the trench;

a second semiconductor layer of a second conductivity type disposed within the trench, wherein the second semiconductor layer is disposed adjacent to the first semiconductor layer and wherein the trench, the first semiconductor layer, and the second semiconductor layer are configured to provide a localized superjunction structure;

a control electrode adjacent the major surface and spaced apart from the localized superjunction structure;

a body region adjacent the major surface, the body region being laterally interposed between the control electrode and the localized superjunction structure, wherein the body region extends from the major surface into the region of semiconductor material to a first depth, and wherein the body region has a vertically oriented side surface adjoining the sidewall surface of the trench; and

a first doped region of the second conductivity type disposed extending from the major surface to a top surface of the second semiconductor layer and to a second depth, wherein the first doped region has a higher dopant concentration than the second semiconductor layer, wherein the second depth is greater than the first depth, and wherein:

a first portion of the first doped region overlaps a top portion of the first semiconductor layer and contacts the sidewall surface of the trench to laterally connect the body region to the second semiconductor layer, the first portion of the first doped region abutting the vertically oriented side surface of the body region,

the top portion of the first semiconductor layer laterally separates a second portion of the first doped region from at least a portion of the vertically oriented side surface of the body region, the second portion of the first doped region being different from the first portion of the first doped region, and

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the first doped region is configured to provide a charge imbalance within the localized superjunction structure.

8. The semiconductor device structure of claim 7, wherein the higher dopant concentration of the first doped region provides the charge imbalance between 5% and 10%.

9. The semiconductor device structure of claim 7, further comprising:

a source region adjacent the body region, wherein: the second depth is between 5 microns and 15 microns.

10. A semiconductor device comprising:

a region of semiconductor material having a major surface; a trench extending from the major surface into the region of semiconductor material, wherein the trench has a sidewall surface;

a superjunction structure disposed in the trench and comprising a first conductivity type region along the sidewall surface of the trench and having a generally vertical orientation, the superjunction structure further comprising a second conductivity type region adjacent to the first conductivity type region;

a body region adjacent the major surface and the superjunction structure, the body region being configured to form a channel region, wherein the body region has a vertically oriented side surface adjoining the trench;

a control electrode adjoining a portion of the body region;

a source region adjacent the body region; and

a first doped structure extending from the major surface to a top surface of the second conductivity type region and configured to create a charge imbalance within an upper portion of the superjunction structure, wherein the first doped structure has a dopant concentration higher than the second conductivity type region, and wherein:

a first portion of the first doped structure overlaps a top portion of the first conductivity type region and contacts the sidewall surface of the trench to laterally connect the body region to the second conductivity

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type region, the first portion of the first doped structure abutting the vertically oriented side surface of the body region, and

the top portion of the first conductivity type region laterally separates a second portion of the first doped structure from at least a portion of the vertically oriented side surface of the body region, the second portion of the first doped structure being different from the first portion of the first doped structure.

11. The device of claim 10, further comprising a second doped structure in the region of semiconductor material below the body region, the second doped structure being configured to connect a drain end of the channel region to the superjunction structure.

12. The device of claim 10, wherein:

the superjunction structure comprises generally vertically oriented n-type and p-type semiconductor material pillars;

the region of semiconductor material comprises a semiconductor substrate and a semiconductor layer on the semiconductor substrate; and

the superjunction structure is within the semiconductor layer.

13. The device of claim 12, wherein the semiconductor substrate and the semiconductor layer have different conductivity types.

14. The device of claim 10, wherein:

the first doped structure extends from the major surface to a first depth;

the body region extends from the major surface to a second depth; and

the first depth is greater than the second depth.

15. The device of claim 14, wherein the first depth is between 5 microns and 15 microns.

16. The device of claim 10, wherein the charge imbalance is between 5% and 10%.

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